BRCS080N04ZB

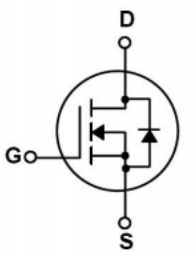
Rev.A May.-2022

DATA SHEET

N-Channel Enhancement Mode Field Effect Transistor in a DFN3 3A-8L Plastic Package.

V_{DS} (V) = 40V
I_D = 40A (V_{GS} = ±20V)

Suited for low voltage applications such as automotive, DC/DC Converters, and high efficiency switching for power management in portable and battery operated products.





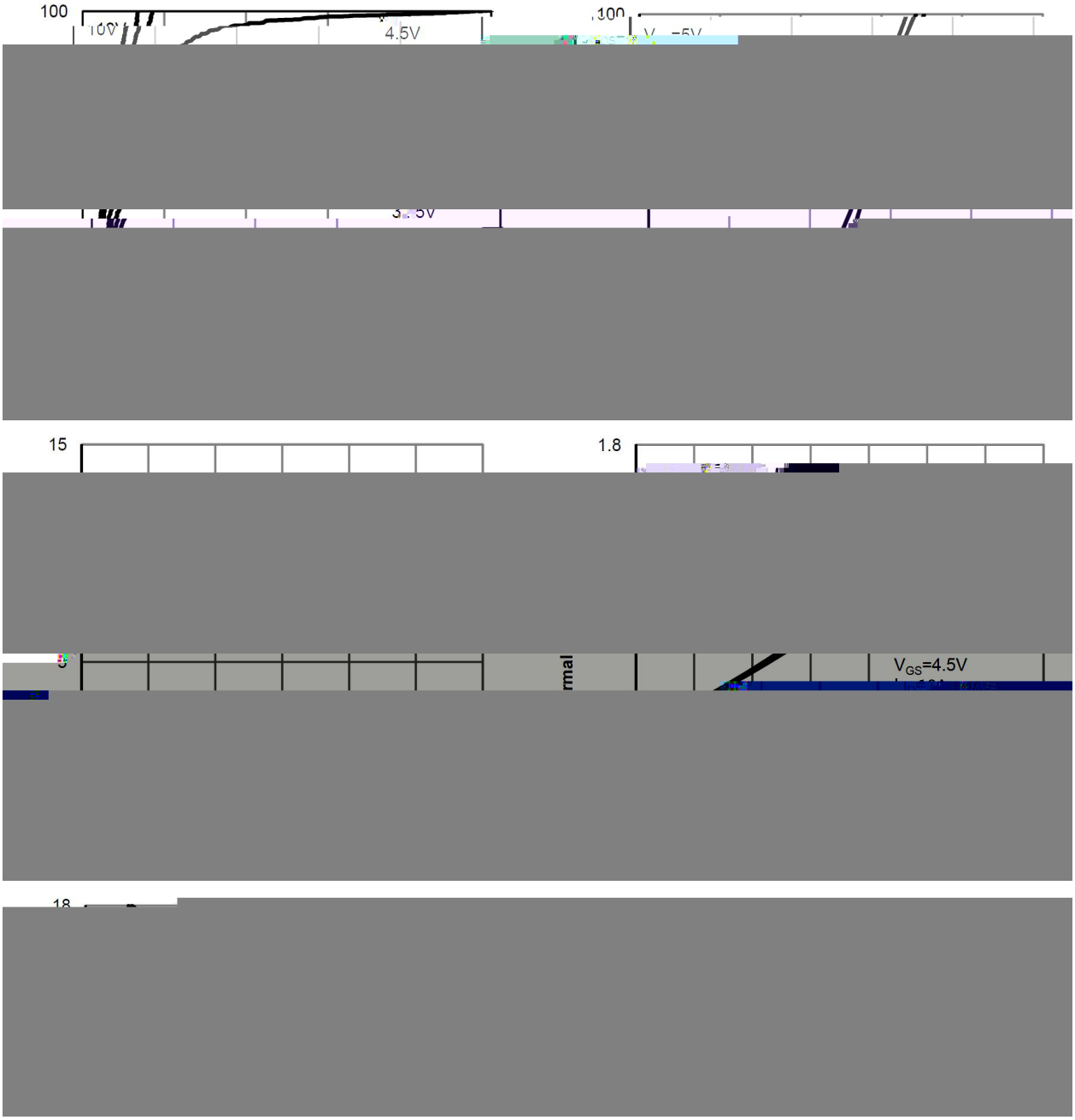
/ Marking

See Marking Instructions.

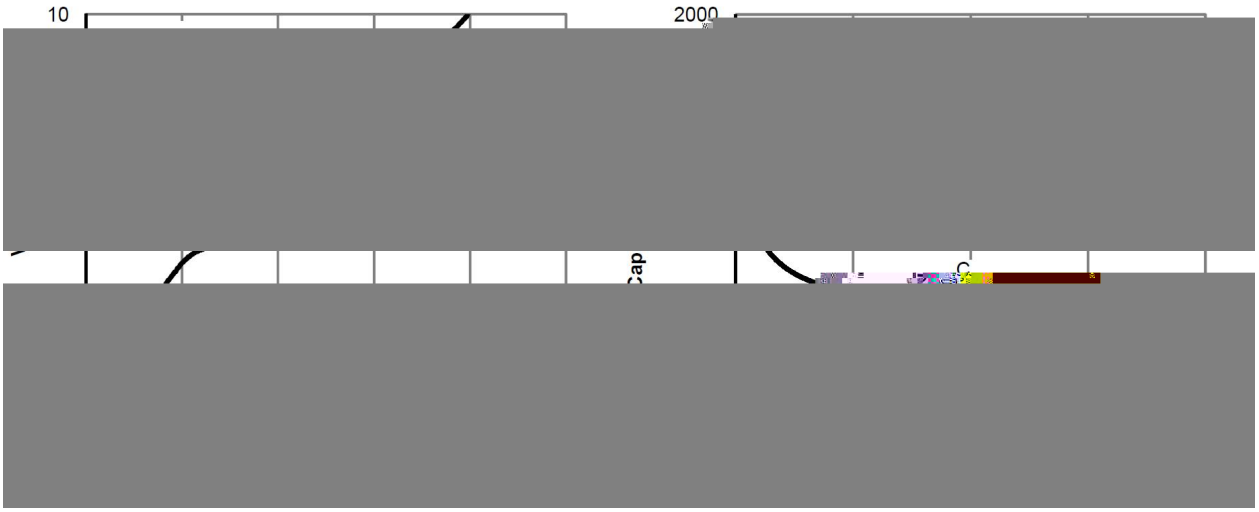
/ Electrical Characteristics(Ta=25)

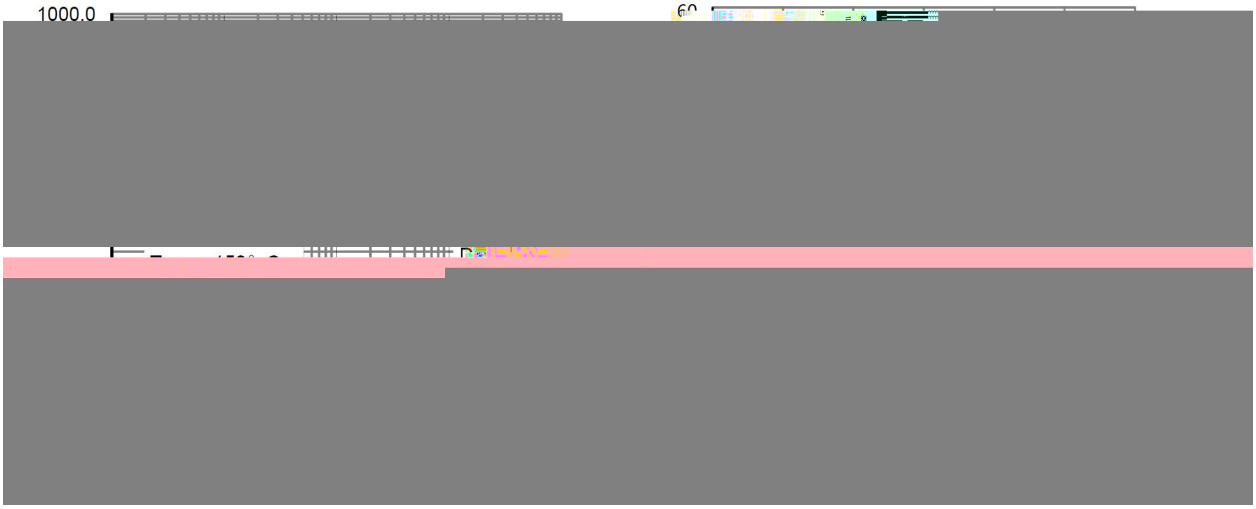
Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Total Gate Charge	$Q_{g(10V)}$	V_{DS}=20V V_{GS}=4.5V I_D=20A		20		nC
Total Gate Charge	$Q_{g(4.5V)}$			8.5		
Gate-Source Charge	Q_{gs}			5.5		
Gate-Drain Charge	Q_{gd}			3		

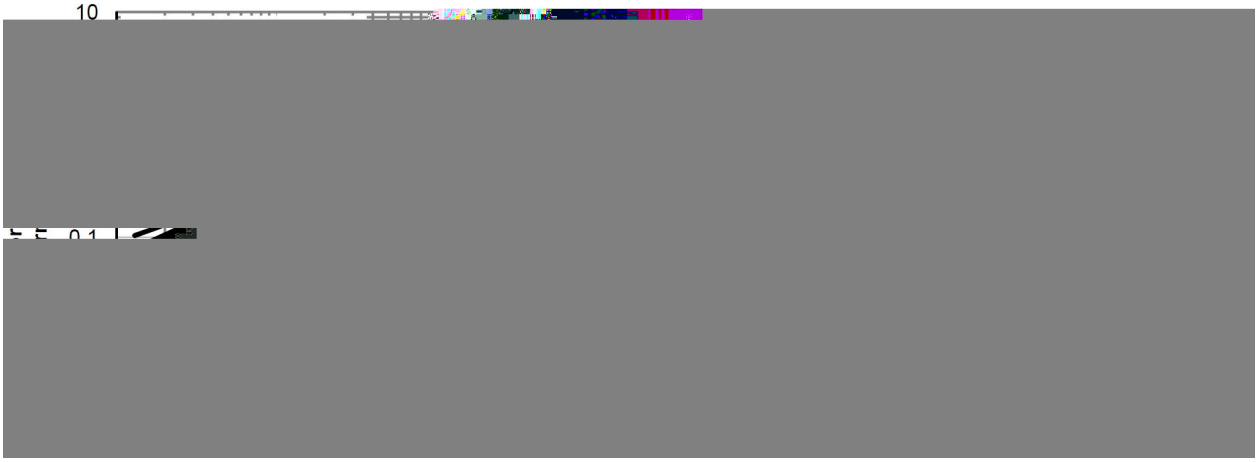
/ Electrical Characteristic Curve



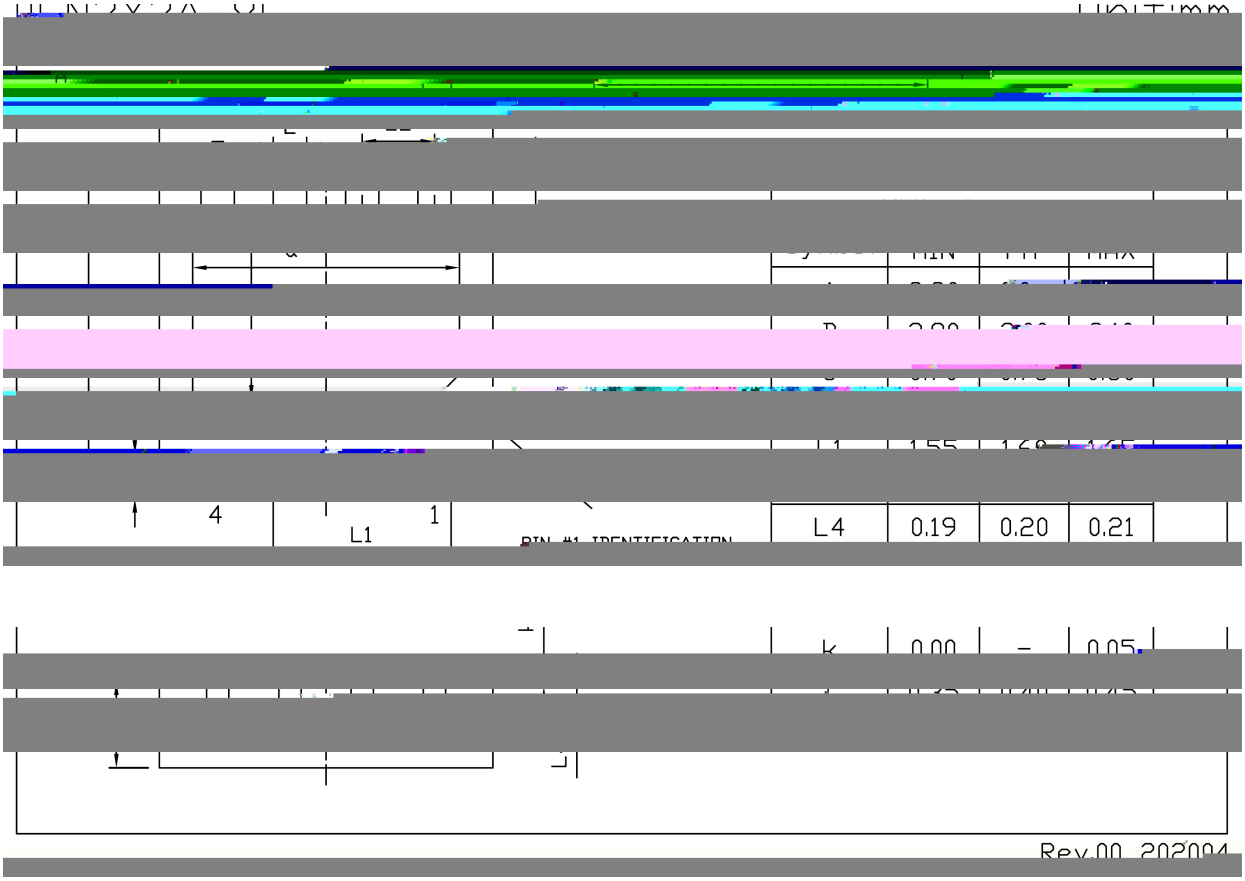
/ Electrical Characteristic Curve



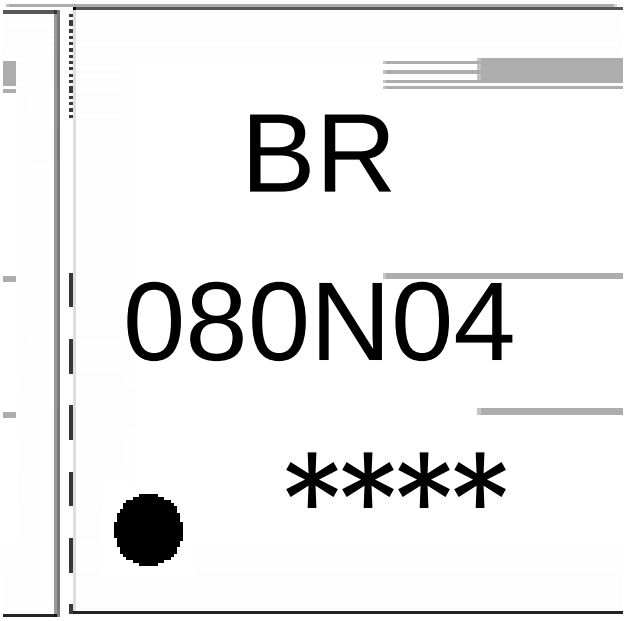




/ Package Dimensions



/ Marking Instructions



BR
080N04
****

Note:

BR:	Company Code.
080N04:	Product Type
****:	Lot No. Code, code change with Lot No.

( ) / Temperature Profile for IR Reflow Soldering(Pb-Free)



						Note:
1		150	180		60 90sec;	1.Preheating:150~180℃, Time:60~90sec.
2		245±5			5±0.5sec;	2.Peak Temp.:245±5℃, Duration:5±0.5sec.
3				2	10℃/sec.	3. Cooling Speed: 2~10℃/sec.

/ Resistance to Soldering Heat Test Conditions

260±5℃	10±1 sec.	Temp.:260±5℃	Time:10±1 sec

/ Packaging SPEC.

/ REEL

Package Type !	Units " # $	Dimension " % & (unit ' mm^3)